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	Filing Date		2006-06-07
	First Named Inventor	Tetsuo Fujii et al.	
	Art Unit	2815	
	Examiner Name	Jerome Jackson Jr.	
	Attorney Docket Number	30794.108-US-WO	

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4	SCHNITZER et al., "30% external quantum efficiency from surface textured, thin-film light-emitting diodes," Appl. Phys. Lett. 63 (16), 18 October 1993, pp. 2174-2176.	<input type="checkbox"/>
5	YAMADA et al., "InGaN-based near-ultraviolet and blue-light-emitting diodes with high external quantum efficiency using a patterned sapphire substrate and a mesh electrode," Jpn. J. Appl. Phys., vol. 41, 2002, pp. L1431-L1433.	<input type="checkbox"/>
6	QI et al., "Study on the formation of dodecagonal pyramid on nitrogen polar GaN surface etched by hot H3PO4," Applied Physics Letters, 95, 2009, pp. 071114-1-071114-3.	<input type="checkbox"/>
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